

• General Description

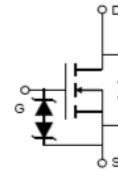
The ZM8810T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

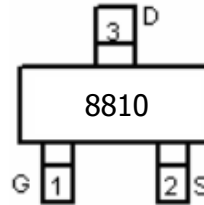
- Load Switch
- PWM Application

• Product Summary


$V_{DS} = 20V$

$R_{DS(ON)} = 16m\Omega$

$I_D = 7A$


SOT23-3
• Ordering Information:

Part NO.	ZM8810T
Marking	ZM8810
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	7	A
	$I_{D@TC=75^\circ C}$	5.3	A
	$I_{D@TC=100^\circ C}$	4.4	A
Pulsed Drain Current ^①	I_{DM}	25	A
Total Power Dissipation ^②	P_D	12	W
Total Power Dissipation($T_A=25^\circ C$)	$P_D@T_A=25^\circ C$	0.75	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	10	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	170	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	0.45	0.6	1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =6A		16	20	mΩ
		V _{GS} =2.5V, I _D =6A		19	25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =1A		50		s
Source-drain voltage	V _{SD}	I _S =6A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	1295	-	pF
Output capacitance	C _{oss}		-	160	-	
Reverse transfer capacitance	C _{rss}		-	87	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} =10V	-	10	14	nC
Gate - Source charge	Q _{gs}	I _D = 7A	-	4.2	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 4.5V	-	2.6	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Power Dissipation Derating Curve

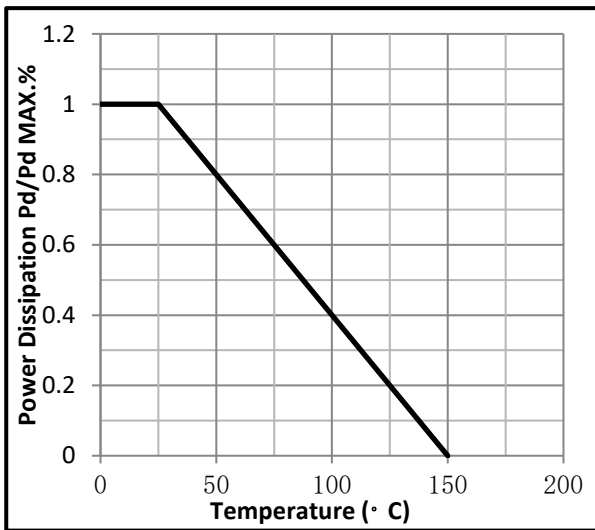


Fig.2 Typical output Characteristics

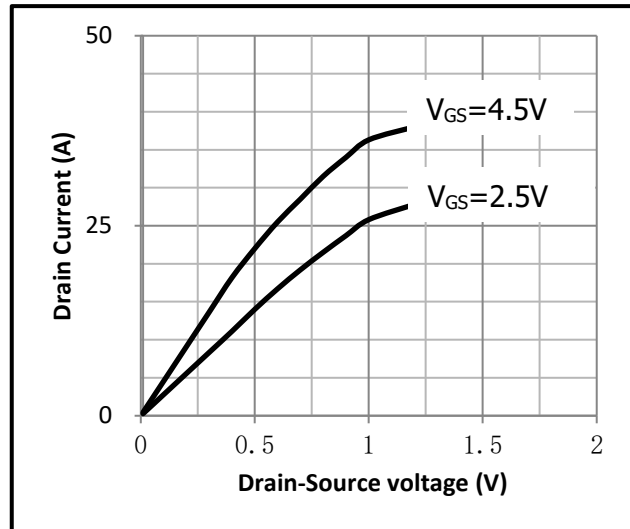


Fig.3 Threshold Voltage V.S Junction Temperature

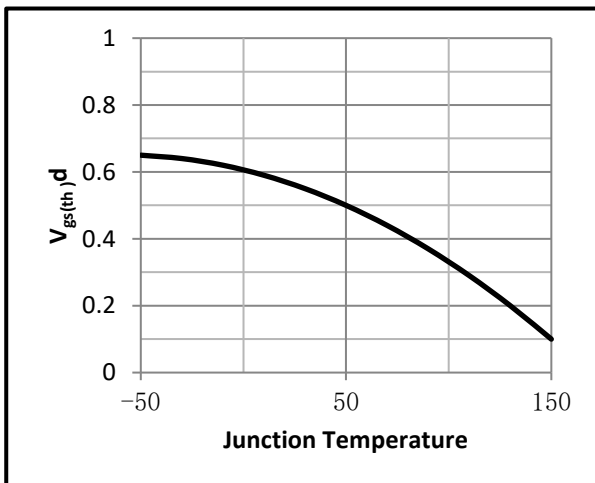


Fig.4 Resistance V.S Drain Current

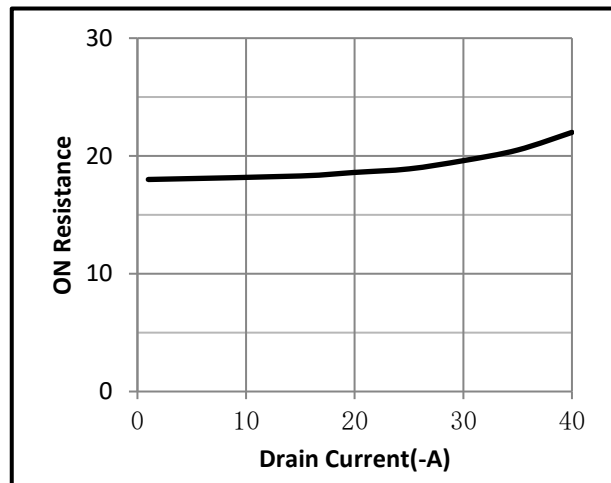


Fig.5 On-Resistance VS Gate Source Voltage

Fig.6 On-Resistance V.S Junction Temperature

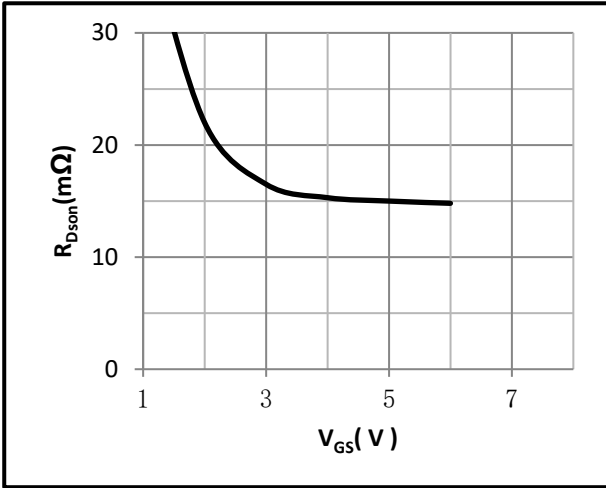


Fig.7 Switching Time Measurement Circuit

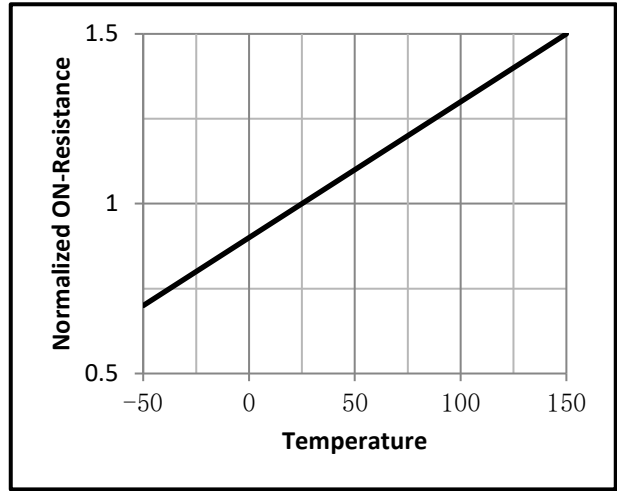


Fig.8 Gate Charge Waveform

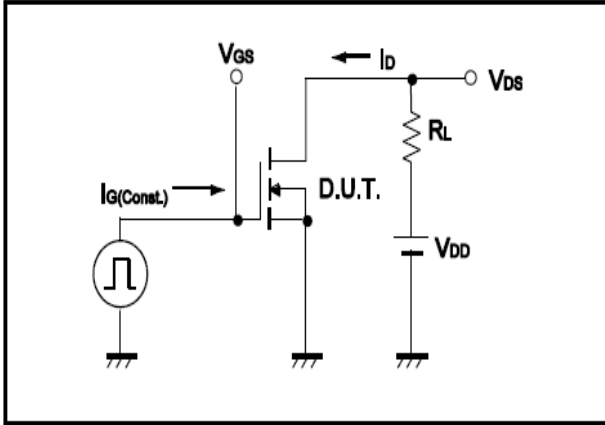


Fig.9 Switching Time Measurement Circuit

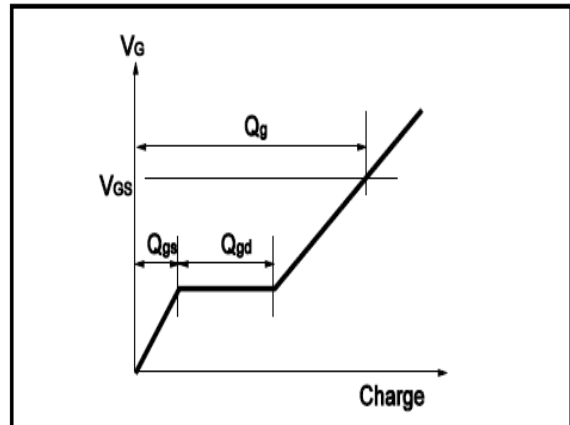


Fig.10 Gate Charge Waveform

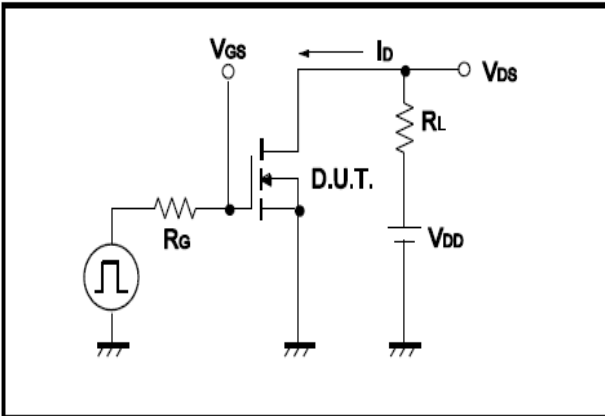


Fig.11 Avalanche Measurement Circuit

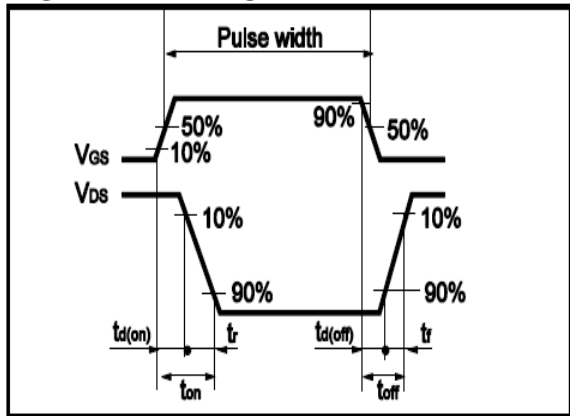
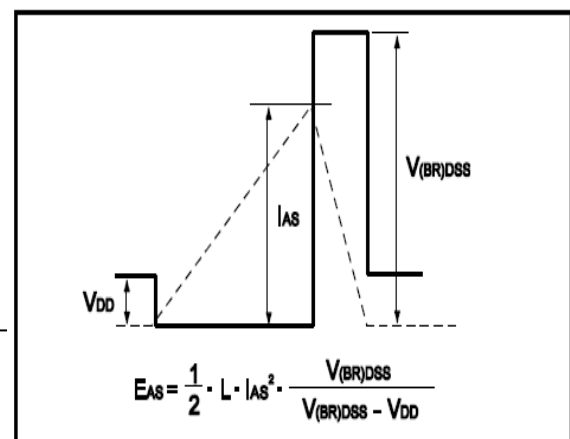
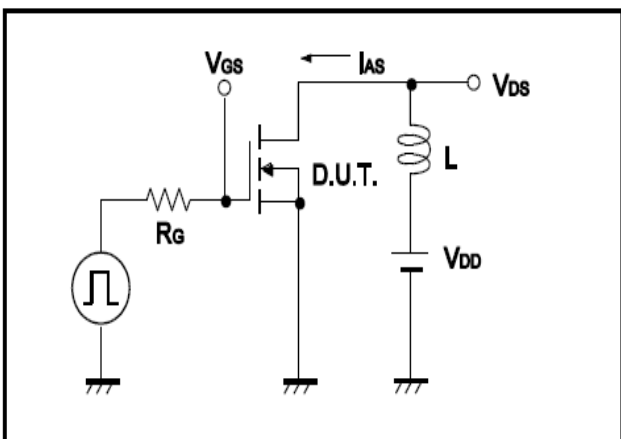


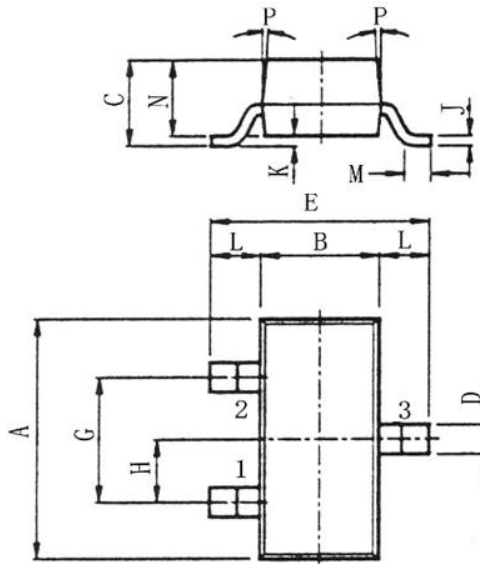
Fig.12 Avalanche Waveform





•Dimensions(SOT23-3)

Unit: mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20



K	0.00		0.10
L	0.45	0.55	0.65
M	0.20		
N	0.90	1.00	1.20
P		7°	